applied surface science

A journal devoted to the properties of interfaces in relation to the synthesis and behaviour of materials



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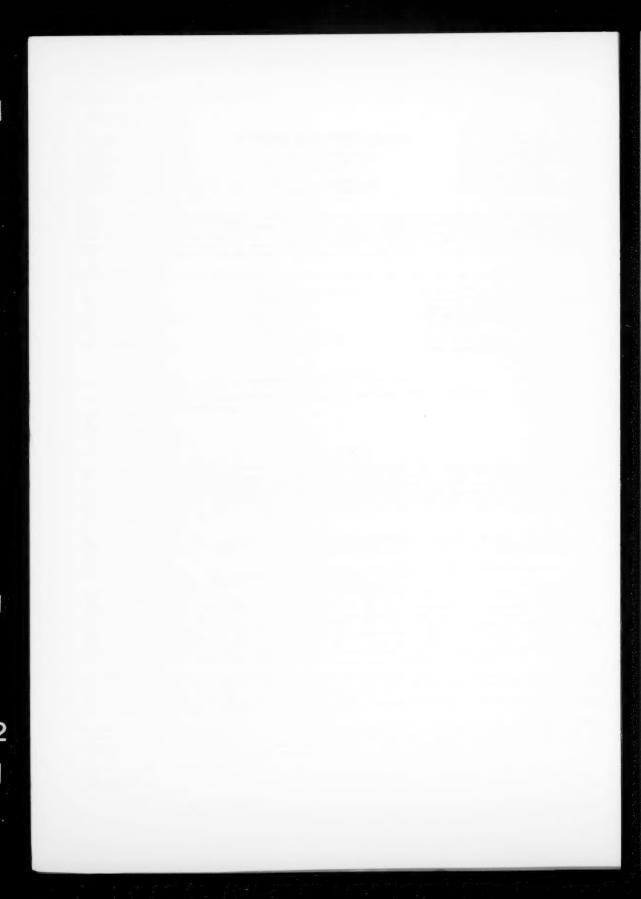
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A JOURNAL DEVOTED TO THE PROPERTIES OF INTERFACES IN RELATION TO THE SYNTHESIS AND BEHAVIOUR OF MATERIALS

Editors:

L.C. Feldman, Murray Hill, NJ, USA J. Nishizawa, Sendai, Japan W.F. van der Weg, Utrecht, The Netherlands

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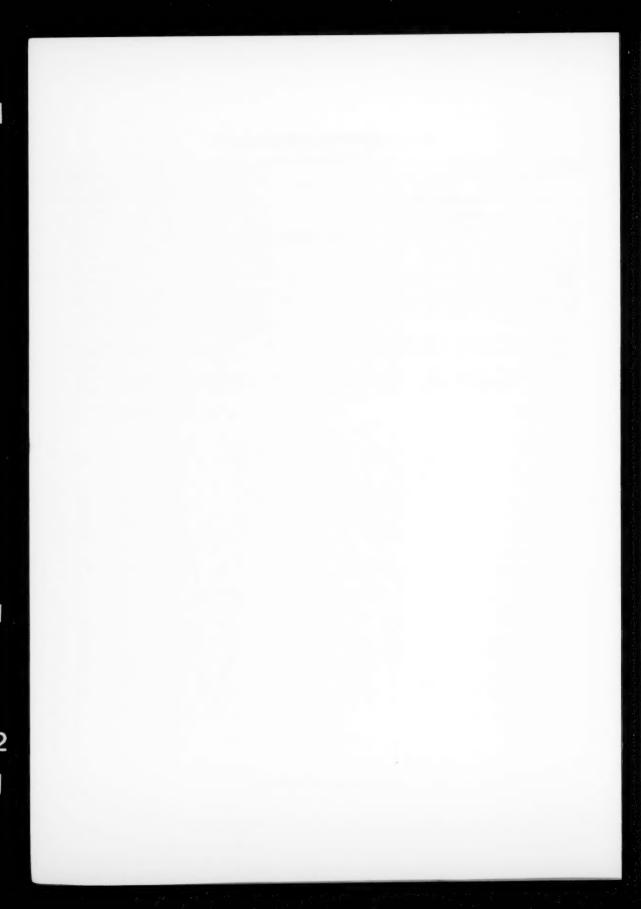
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Adhesion

Adsorption isotherms

Alkali halides

Alkali metals

Allovs

Aluminium

Aluminium oxide

Ammonia

Amorphous materials

Annealing

Antimony

Arsenic

Atomic force microscopy

Auger electron spectroscopy

Band structure

Barium

Bervllium

Bismuth

Borides

Boron

Boron nitride

Cadmium selenide

Cadmium sulphide

Cadmium telluride

Carbides

Carbon

Carbon monoxide

Carboxylic acid

Catalysis

Cathodes

Ceramics

Chalcogenides

Chemical vapour deposition

Chemisorption theory

Chromium

Clusters

Coatings

Cobalt

Cobalt oxide

Compound formation

Computer simulations

Copper

Corrosion

Crystallization

Cuprous oxide

Diamond

Dielectric constant

Diffusion

Doping effects

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Electron spin resonance

Electron stimulated desorption

Ellipsometry

Epitaxy

Etching

Evaporation

Field emission

Field emission microscopy

Field ion microscopy

Field ionisation

Gallium

Gallium antimonide

Gallium arsenide

Gallium phosphide

C III

Gallium selenide

Germanium

Glass

Gold

Grain boundary Graphite

Halides
Hall effect
Halogenides
Halogens
Heterostructures
Hydrides
Hydrocarbons
Hydrogen

Hydrogen sulphide

Indium
Indium arsenide
Indium oxide
Indium phosphide
Infrared spectroscopy
Inorganic compounds

Insulator-semiconductor interfaces

Interfaces
Ion bombardment
Ion implantation
Ion scattering
Iridium
Iron
Iron oxide

Lanthanides Laser processing

Lead
Lead oxide
Light scattering
Luminescence

Magnesium Magnesium oxide Magnetic measurements Magnetic structures Manganese

Mass spectroscopy Mercury telluride

Metal-oxide-semiconductor structure (MOS)

Metals

Metal-semiconductor interfaces

Methane Mica

Molecular beam epitaxy

Molybdenum

Mössbauer spectroscopy

Multilayers

Neutron scattering

Nickel
Nickel oxide
Niobium
Niobium oxide
Nitric oxide
Nitrides
Nitrogen
Nitrous oxide

Nuclear magnetic resonance

Nucleation

Optical properties Organic substances

Organometallic vapour deposition

Oxidation Oxides Oxygen Ozone

Palladium Phosphine Phosphorus Photoconductivity Photodesorption

Photoelectron spectroscopy

Photon emission Plasma processing Platinum

Ouantum effects

Polymers

Radiation damage Raman scattering Reflection spectroscopy

Rhenium Rhodium Ruthenium

Scandium Schottky barrier

Second harmonic generation Secondary ion mass spectroscopy

Selenium

Semiconductors

Semiconductor-semiconductor interfaces

Silane Silicides Silicon

Silicon carbide Silicon nitride Silicon oxide

Silver Sintering

Solid-electrolyte interface

Solid phase epitaxy Sputter deposition

Sputtering Steel Sulphides Sulphur

Superconductivity Superlattices

Surface and interface states

Surface composition Surface defects Surface diffusion Surface energy Surface morphology

Surface phonons and adsorbate vibrations

Surface photovoltage Surface plasmons Surface roughness Surface segregation Surface structure Surface thermodynamics Tantalum Tellurium

Thermal desorption

Thin films Tin Tin oxide Titanium

Titanium
Titanium carbide
Titanium oxide
Tribology
Tungsten
Tungsten oxide
Tunneling

Vanadium Vanadium oxide

Water Wetting Work function

X-ray absorption X-ray diffraction X-ray emission X-ray scattering X-ray spectroscopy

Zeolites Zinc Zirconium

INSTRUCTIONS FOR AUTHORS

Contributions must be written in English and should have an abstract. The original manuscript (with original figures) and two duplicate copies should be submitted to one of the Editors. Micrographs should be submitted in triplicate. See inside front cover for the addresses.

Rapid publication: Short papers, for which rapid publication is appropriate, may be submitted as a "Letter". The manuscripts should not exceed 1000 words in length, contain a modest number of illustrations and a short abstract.

Length of manuscript: Typically 10 pages of manuscript and 4 figures will produce roughly 5 printed pages (count title page, text pages, tables and figure captions as manuscript pages).

Page charge and reprints: There is no page charge and 25 reprints of the article will be supplied free of charge. Additional reprints may be ordered from the publisher. An order form will be sent to contributors together with the proofs.

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Manuscripts should be typed throughout with double line spacing and wide margins on numbered pages.

The title page(s) should contain, in addition to the article title, author(s)' names and affiliations, the text of related footnotes and the text of the abstract. Indicate which author will act as contact author and provide FAX No., telephone No. and telex No., if available.

Tables should be typed on separate sheets at the end of the manuscript. In addition to its serial number, each table should have a sufficiently detailed heading or caption to explain the data displayed in it.

Figures should be numbered and their captions listed together at the end of the manuscript.

References in the text to other publications should be numbered consecutively within square brackets, for example: "Chang and Weaver [1] have shown ..." and listed together at the end of the text, for example:

- [1] S.-C. Chang and M.J. Weaver, Surf. Sci. 241 (1991) 11.
- [2] S.J. Hoekje and G.B. Hoflund, Appl. Surf. Sci. 47 (1991) 43.
- [3] F.J. Himpsel, Surf. Sci. Rep. 12 (1990) 1.
- [4] A. Roth, Vacuum Technology, 3rd ed. (North-Holland, Amsterdam, 1990).
- [5] V. Celli, in: Dynamical Properties of Solids, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

References to unpublished or not readily accessible reports should be avoided. In the case of multiple authorship all authors should be listed in the references provided they number less than ten. Only in the case of more than ten authors is the first author et al. acceptable.

Formulae in the manuscript should be typed with particular consideration given to characters that may be misinterpreted, e.g.

I (cap.), I (el), I (one), ' (prime) c, C; k, I

c, C; k, K, κ (kappa); p, P, ρ (rho) u, v (lower case), ν (nu), V (cap.)

o (lower case), O (cap.), 0 (zero), ° (deg) × (times), x (lower case), X (cap.)

 Σ (sigma), Σ (sum); Π (pi), Π (product); etc.

If necessary, unusual symbols should be explained in pencil in the margin.

Vectors should be indicated by a wavy underlining, and will be printed in bold-face italics.

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The publisher requires a set of good quality drawings and photographs to produce the printed line figures and half-tone plates in the journal. Photographic copies ("glossy prints") of drawings are also acceptable for the line figures if they have been sharply focused and evenly exposed. As a rule, Xerox copies cannot be accepted. Original drawings and photographs will be returned after publication of the paper.

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Figures are preferably reduced to a single column width (7.6 cm) unless their complexity, large width-to-height ratio, or need to display special detail makes a larger format necessary (max. printed width ~ 20 cm). Inappropriately sized lettering on a figure may prevent its reduction to the size optimum for its information content. The lettering used on a drawing should be chosen so that after reduction, the height of numbers and (capital) letters falls within the range 1.2–2.4 mm. Care should be exercised in choosing the pen width of machine-plotted graphs. Frequently lines in these figures are too fine compared to the area of the figure.

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applied surface science

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